

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	87468	(ONO or (oxide adj nitride adj oxide))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/16 10:08
2	BRS	L2	85657	(gate near2 (insulat\$6 or dielectric\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/16 10:09
3	BRS	L3	1478	1 near8 ((control\$6 or float\$6) near2 gate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/16 10:10
4	BRS	L4	533	1 near4 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/16 10:12
5	BRS	L6	289	3 and (1 near4 (peripher\$6 or memory))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/16 10:13

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L5	244	3 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/16 10:14

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L353	289	((((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 (peripher\$6 or memory)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/16 14:25
2	BRS	L354	244	((((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 ((gate near2 (insulat\$6 or dielectric\$6))))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/16 14:25
3	BRS	L355	241	353 not 354	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/16 14:26

(periph\$4 or HV or high near<sup>2</sup> volt\$4)

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	197871 7	memory or CAM or (code near2 address) or RAM or SRAM or flash	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:34
2	BRS	L2	8500	(gate near2 (insulator or dielectride))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:28
3	BRS	L6	87468	(ONO or (oxide adj nitride adj oxide))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:29
4	BRS	L7	85657	(gate near2 (insulat\$6 or dielectric\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:29
5	BRS	L8	1478	((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L9	533	((ONO or (oxide adj nitride adj oxide))) near4 ((gate near2 (insulat\$6 or dielectric\$6)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:29
7	BRS	L10	289	((((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 (peripher\$6 or memory)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:31
8	BRS	L3	15	((ONO or (oxide adj nitride adj oxide))) near8 ((gate near2 (insulator or dielectride))) same (memory or CAM or (code near2 address) or RAM or SRAM or flash)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:29
9	BRS	L11	244	((((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 ((gate near2 (insulat\$6 or dielectric\$6))))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L12	241	((((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and ((ONO or (oxide adj nitride adj oxide))) near4 (peripher\$6 or memory))) not (((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 ((gate near2 (insulat\$6 or dielectric\$6))))))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:29
11	BRS	L13	1137	((((ONO or O-N-O or (oxide near3 nitride near3 oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (periph\$6 or HV or (high near2 volt\$6)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:34
12	BRS	L14	1125	13 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:34
13	BRS	L15	191	((((ONO or O-N-O or (oxide near3 nitride near3 oxide))) near8 ((control\$6 or float\$6) near2 gate)) same (periph\$6 or HV or (high near2 volt\$6)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 10:34

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L301	197871 7	memory or CAM or (code near2 address) or RAM or SRAM or flash	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:02
2	BRS	L302	8500	(gate near2 (insulator or dielectride))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:02
3	BRS	L303	87468	(ONO or (oxide adj nitride adj oxide))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:02
4	BRS	L304	85657	(gate near2 (insulat\$6 or dielectric\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:02
5	BRS	L305	1478	((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:02

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L306	533	((ONO or (oxide adj nitride adj oxide))) near4 ((gate near2 (insulat\$6 or dielectric\$6)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:02
7	BRS	L307	289	((((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 (peripher\$6 or memory)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:02
8	BRS	L311	1137	((((ONO or O-N-O or (oxide near3 nitride near3 oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (periph\$6 or HV or (high near2 volt\$6)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:03
9	BRS	L312	1125	(((((ONO or O-N-O or (oxide near3 nitride near3 oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (periph\$6 or HV or (high near2 volt\$6))) and (memory or CAM or (code near2 address) or RAM or SRAM or flash))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:03
10	BRS	L308	15	((ONO or (oxide adj nitride adj oxide))) near8 ((gate near2 (insulator or dielectride))) same (memory or CAM or (code near2 address) or RAM or SRAM or flash)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:03



	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L309	244	((((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 ((gate near2 (insulat\$6 or dielectric\$6)))))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:03
12	BRS	L310	241	(((((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 (peripher\$6 or memory))) not (((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 ((gate near2 (insulat\$6 or dielectric\$6)))))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:03
13	BRS	L313	191	((((ONO or O-N-O or (oxide near3 nitride near3 oxide))) near8 ((control\$6 or float\$6) near2 gate)) same (periph\$6 or HV or (high near2 volt\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:08
14	BRS	L314	245	(ONO or O-N-O or (oxide near3 nitride near3 oxide)) near4 (periph\$6 or HV or (high near2 volt\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/17 15:10

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	161	(438/142).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B
2	IS&R	L2	201	(438/263).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B
3	IS&R	L3	614	(438/258).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B
4	IS&R	L4	1476	(438/257).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B
5	IS&R	L5	170	(438/211).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
6	IS&R	L6	507	(438/756) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B
7	IS&R	L7	143	(438/757) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B